

Silicon NPN Power Transistors

2SC1942

DESCRIPTION

- With TO-3 package
- High breakdown voltage
- High speed switching

APPLICATIONS

- For TV horizontal output applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

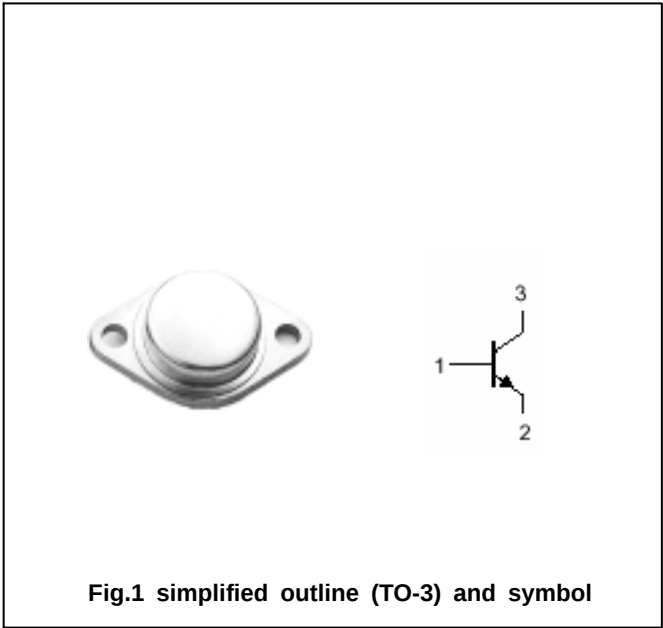


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3	A
P _T	Total power dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	2.5	/W

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.1A$; $I_B=0$	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2.5A$; $I_B=0.8A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2.5A$; $I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=600V$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			10	μA
h_{FE}	DC current gain	$I_C=1A$; $V_{CE}=5V$	8		40	

固电半导体

INCHANGE SEMICONDUCTOR

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PACKAGE OUTLINE

